

Amendments to the Specification:

Page 14, amend the paragraph beginning on line 17 to read as follows:

We will now describe in detail a plasma etching apparatus utilizing electromagnetic waves in the UHF band, which is one example of the plasma processing apparatus according to a first preferred embodiment of the present invention with reference to FIG. 1. The plasma etching apparatus is composed of a reaction chamber container 10 defining a reaction chamber 1, a dielectric vacuum window 12, a gas discharge plate 13 having gas discharge holes 131, a wafer holding electrode 14 functioning as a substrate holder on which a wafer 4 is mounted, a field coil 15, an exhaust outlet 16 for maintaining the inside of the reaction chamber container 10 in decompressed state, a plasma-generating high-frequency electrode 17 to which high frequency is applied from a plasma-generating high-frequency power supply 18 for generating plasma 9 inside the reaction chamber, a wafer biasing high-frequency power supply 19 for supplying a biasing high-frequency power to the wafer holding electrode 14, and a conductive portion or member 21a electrically connected to the reaction chamber container 10 and functioning as a DC earth. The surface portion of an inner wall 101 of the reaction chamber container 10 which is exposed to the plasma is coated with insulating material 102.